Appl. No. 10/595,703 Amdt. dated March 11, 2009 Reply to Office action of January 14, 2009

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1 1. (Currently Amended) A method comprising the steps of:
- 2 (a) simulating on a processor a fabrication of a plurality of layout patterns by a lithographic
- 3 process;
- 4 (b) determining sensitivities of the layout patterns to a plurality of parameters based on the
- 5 simulation simulating;
- 6 (c) using the sensitivities to calculate deviations of the <u>layout</u> patterns across a range of each
- 7 respective one of the parameters; and
- 8 (d) selecting ones of the <u>layout</u> patterns having predetermined deviation characteristics to be
- 9 used as test patterns.
- 1 2. (Original) The method of claim 1, further comprising applying optical proximity
- 2 correction, and repeating steps (a) through (d).
- 1 3. (Currently Amended) The method of claim 1, wherein step (b) includes calculating the
- 2 sensitivity of one of the patterns one pattern of the layout patterns with respect to one of the
- 3 parameters as a partial derivative of the deviation a deviation of the one pattern with respect to
- 4 the one parameter one of the parameters, based on only two values of the one parameter one of
- 5 <u>the parameters</u> and the corresponding two values of the deviation of the one pattern.
- 1 4. (Currently Amended) The method of claim 1, wherein step (c) includes calculating the
- 2 deviations of the <u>layout patterns</u> using a first degree polynomial that is a linear combination
- 3 of deviation portions due to each respective parameter, each respective deviation calculated
- 4 based on the respective sensitivity of the pattern one pattern of the layout patterns to that
- 5 parameter.

Appl. No. 10/595,703 Amdt. dated March 16, 2009 Reply to Office action of January 14, 2009

- 1 5. (Currently Amended) The method of claim 1, further comprising automatically selecting
- 2 the patterns ones of the layout patterns having maximum or near-maximum deviations to be used
- 3 as test patterns.
- 1 6. (Currently Amended) The method of claim 5, further comprising printing the patterns the
- 2 ones of the layout patterns having maximum or near-maximum deviations on a test chip or test
- 3 wafer.
- 1 7. (Currently Amended) The method of claim 1, further comprising selecting a plurality of
- 2 directions, and selecting the respective <u>layout</u> patterns having the maximum deviation in each
- 3 respective one of the plurality of directions to be used as test patterns.
- 1 8. (Currently Amended) The method of claim 1, wherein the predetermined deviation
- 2 characteristics are selected from the group a group consisting of maximum, near maximum,
- 3 minimum and near minimum deviations in a multidimensional process parameter space.
- 1 9. (Original) The method of claim 1, wherein the patterns are selected so as to have
- 2 extremal sensitivities with respect to deviations in process parameters.
 - 10. (Currently Amended) A computer-implemented system comprising:
- 2 means for simulating on a processor a fabrication of a plurality of layout patterns by a
- 3 lithographic process;

1

- 4 means for determining sensitivities of the layout patterns to a plurality of parameters
- 5 based on the <u>simulation simulating</u>;
- 6 means for using the sensitivities to calculate deviations of the <u>layout</u> patterns across a
- 7 range of each respective one of the parameters; and
- 8 means for selecting ones of the <u>layout</u> patterns having predetermined deviation
- 9 characteristics to be used as test patterns.

Appl. No. 10/595,703 Amdt. dated March 16, 2009 Reply to Office action of January 14, 2009

- 1 11. (Currently Amended) A computer-readable medium encoded with computer program
- 2 code, wherein, when the computer program code is executed by a processor, the processor
- 3 performs a method comprising the steps of:
- 4 (a) simulating on a processor a fabrication of a plurality of layout patterns by a lithographic
- 5 process;
- 6 (b) determining sensitivities of the layout patterns to a plurality of parameters based on the
- 7 simulation simulating;
- 8 (c) using the sensitivities to calculate deviations of the <u>layout</u> patterns across a range of each
- 9 respective one of the parameters; and
- 10 (d) selecting ones of the <u>layout</u> patterns having predetermined deviation characteristics to be
- 11 used as test patterns.
- 1 12. (Currently Amended) A computer implemented system comprising:
- 2 means for receiving a set of priorities from a user;
- means for selecting a subset of features of a mask having the highest error rates, using a
- 4 plurality of layout data;
- 5 means for constructing an extrema map consistent with the user input; a user input
- 6 including the set of priorities; and
- 7 means for identifying one or more changes to the layout data based on the extrema map.
- 1 13. (Currently Amended) The computer implemented system of claim 12, further comprising
- 2 means for systematically selecting characterizing structures from a layout that is generated from
- 3 the layout data, the characterizing structures characterizing the lithography and process
- 4 performance of the layout.
- 1 14. (Currently Amended) The computer implemented system of claim 13, wherein the
- 2 selecting of characterizing structures is based on lithographical properties of the characterizing
- 3 structures.

Appl. No. 10/595,703 Amdt. dated March 16, 2009 Reply to Office action of January 14, 2009

- 1 15. (Currently Amended) The <u>computer implemented</u> system of claim 13 14, wherein the
- 2 characterizing structures are selected based on the lithographical properties of the characterizing
- 3 structures under variation of a plurality of process parameters.
- 1 16. (Currently Amended) The <u>computer implemented</u> system of claim 15, wherein the
- 2 selection selecting of characterizing structures includes: characterizing each process
- 3 parameter by a respective sensitivity of the pattern layout pattern to changes of that process
- 4 parameter; and
- 5 selecting a hull of a multi-dimensional process space by combining the sensitivities and
- 6 determining maximum and/or minimum values of the combined sensitivities.
- 1 17. (Currently Amended) The <u>computer implemented</u> system of claim 16, wherein a function
- 2 modeling non-monotonic sensitivity to one of the process parameters is defined using sampled
- 3 extrema points.
- 1 18. (Currently Amended) The computer implemented system of elaim 14 claim 15, wherein
- 2 measurements are used to calibrate the process parameters.
- 1 19. (Currently Amended) The computer implemented system of claim 18, wherein the
- 2 measurements are deviations in distance, covered area or critical dimension.
- 1 20. (Currently Amended) An integrated circuit fabricated by a method comprising:
- 2 (a) simulating a fabrication of a plurality of layout patterns by a lithographic process;
- 3 (b) determining sensitivities of the layout patterns to a plurality of parameters based on the
- 4 simulatingsimulation;
- 5 (c) selecting ones of the <u>layout patterns</u> to be used as test patterns based on the sensitivities;
- 6 (d) fabricating the selected test patterns in an apparatus that performs the lithographic
- 7 process;
- 8 (e) performing an inspection of on the fabricated test patterns;

ATTORNEY DOCKET NO.: D5116-00046

Appl. No. 10/595,703 Amdt. dated March 11, 2009 Reply to Office action of January 14, 2009

- 9 (f) adjusting the lithographic process based on the inspection; and
- 10 (g) fabricating an integrated circuit in the apparatus using the adjusted lithographic process.